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(54) CONFINED CELL STRUCTURES AND METHODS OF FORMING CONFINED CELL STRUCTURES

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(57) **ABSTRACT**

Techniques for reducing damage in memory cells are provided. Memory cell structures are typically formed using dry etch and/or planarization processes which damage certain regions of the memory cell structure. In one or more embodiments, certain regions of the cell structure may be sensitive to damage. For example, the free magnetic region in magnetic memory cell structures may be susceptible to demagnetization. Such regions may be substantially confined by barrier materials during the formation of the memory cell structure, such that the edges of such regions are protected from damaging processes. Furthermore, in some embodiments, a memory cell structure is formed and confined within a recess in dielectric material.